Vishay Semiconductors



Silicon NPN Phototransistor, RoHS Compliant



DESCRIPTION

BPW76 is a silicon NPN phototransistor with high radiant sensitivity in hermetically sealed TO-18 package with base terminal and flat glass window. It is sensitive to visible and near infrared radiation.

FEATURES

Package type: leadedPackage form: TO-18

• Dimensions (in mm): Ø 4.7

· High photo sensitivity

· High radiant sensitivity

· Suitable for visible and near infrared radiation

· Fast response times

• Angle of half sensitivity: $\phi = \pm 40^{\circ}$

· Base terminal connected

· Hermetically sealed package

· Flat glass window

 Lead (Pb)-free component in accordance with RoHS 2002/95/EC and WEEE 2002/96/EC

APPLICATIONS

· Detector in electronic control and drive circuits

PRODUCT SUMMARY					
COMPONENT	I _{ca} (mA)	φ (deg)	λ _{0.1} (nm)		
BPW76A	0.4 to 0.8	± 40	450 to 1080		
BPW76B	> 0.6	± 40	450 to 1080		

Note

Test condition see table "Basic Characteristics"

ORDERING INFORMATION						
ORDERING CODE	PACKAGING	REMARKS	PACKAGE FORM			
BPW76A	Bulk	MOQ: 1000 pcs, 1000 pcs/bulk	TO-18			
BPW76B	Bulk	MOQ: 1000 pcs, 1000 pcs/bulk	TO-18			

Note

MOQ: minimum order quantity

ABSOLUTE MAXIMUM RATINGS						
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT		
Collector base voltage		V _{CBO}	80	V		
Collector emitter voltage		V _{CEO}	70	V		
Emitter base voltage		V _{EBO}	5	V		
Collector current		I _C	50	mA		
Collector peak current	$t_p/T = 0.5, t_p \le 10 \text{ ms}$	I _{CM}	100	mA		
Total power dissipation	T _{amb} ≤ 25 °C	P _V	250	mW		
Junction temperature		Tj	125	°C		
Operating temperature range		T _{amb}	- 40 to + 125	°C		
Storage temperature range		T _{stg}	- 40 to + 125	°C		
Soldering temperature	t ≤ 5 s	T _{sd}	260	°C		
Thermal resistance junction/ambient	Connected with Cu wire, 0.14 mm ²	R _{thJA}	400	K/W		
Thermal resistance junction/gase		R _{thJC}	150	K/W		

Note

Downloaded from Arrow.com.

T_{amb} = 25 °C, unless otherwise specified



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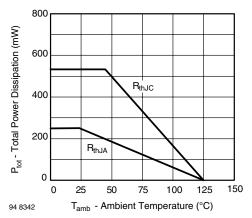


Fig. 1 - Power Dissipation Limit vs. Ambient Temperature

BASIC CHARACTERISTICS						
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Collector emitter breakdown voltage	I _C = 1 mA	V _{(BR)CEO}	70			V
Collector emitter dark current	V _{CE} = 20 V, E = 0	I _{CEO}		1	100	nA
Collector emitter capacitance	V _{CE} = 5 V, f = 1 MHz, E = 0	C _{CEO}		6		pF
Angle of half sensitivity		φ		± 40		deg
Wavelength of peak sensitivity		λ_{p}		850		nm
Range of spectral bandwidth		λ _{0.1}		450 to 1080		nm
Collector emitter saturation voltage	$E_{e} = 1 \text{ mW/cm}^{2}, \lambda = 950 \text{ nm}, I_{C} = 0.1 \text{ mA}$	V _{CEsat}		0.15	0.3	V
Turn-on time	$V_S = 5 \text{ V}, I_C = 5 \text{ mA}, R_L = 100 \Omega$	t _{on}		6		μs
Turn-off time	$V_S = 5 \text{ V}, I_C = 5 \text{ mA}, R_L = 100 \Omega$	t _{off}		5		μs
Cut-off frequency	$V_S = 5 \text{ V}, I_C = 5 \text{ mA}, R_L = 100 \Omega$	f _c		110		kHz

Note

 T_{amb} = 25 °C, unless otherwise specified

TYPE DEDICATED CHARACTERISTICS							
PARAMETER	TEST CONDITION	PART	SYMBOL	MIN.	TYP.	MAX.	UNIT
Collector light ourrent	$E_e = 1 \text{ mW/cm}^2, \lambda = 950 \text{ nm},$	BPW76A	I _{ca}	0.4		0.8	mA
Collector light current	$V_{CE} = 5 V$	BPW76B	I _{ca}	0.6			mA

BASIC CHARACTERISTICS

T_{amb} = 25 °C, unless otherwise specified

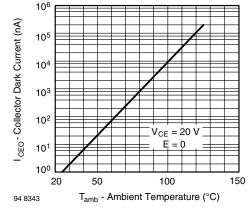


Fig. 2 - Collector Dark Current vs. Ambient Temperature

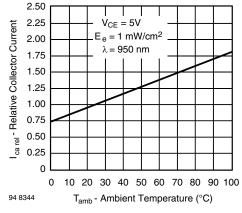


Fig. 3 - Relative Collector Current vs. Ambient Temperature

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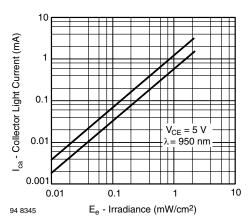


Fig. 4 - Collector Light Current vs. Irradiance

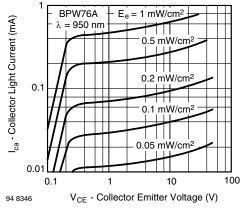


Fig. 5 - Collector Light Current vs. Collector Emitter Voltage

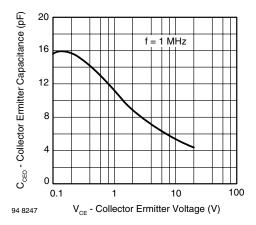


Fig. 6 - Collector Emitter Capacitance vs. Collector Emitter Voltage

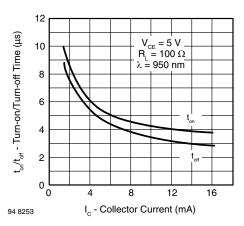


Fig. 7 - Turn-on/Turn-off Time vs. Collector Current

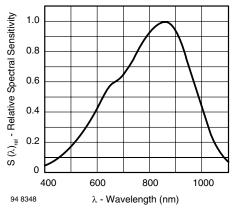


Fig. 8 - Relative Spectral Sensitivity vs. Wavelength

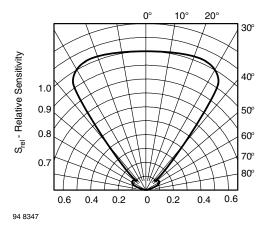
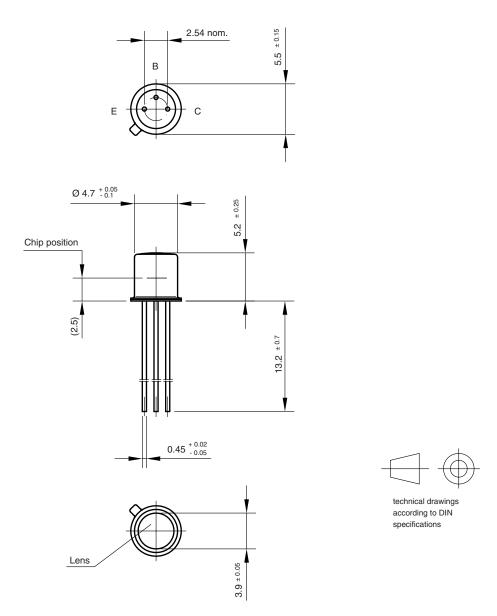


Fig. 9 - Relative Radiant Sensitivity vs. Angular Displacement



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PACKAGE DIMENSIONS in millimeters



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